



#### 60V NPN LOW VCESAT TRANSISTOR IN PowerDI3333-8

#### **Features**

- BV<sub>CEO</sub> > 60V
- Small Form Factor Thermally Efficient Package.
   Enables Higher Density End Products
- I<sub>C</sub> = 6A high Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 60mV @ 1A</li>
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: DXTP03060CFG
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.03 grams (Approximate)

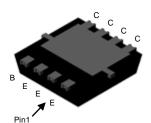
#### **Applications**

- MOSFET & IGBT Gate Drivers
- · Solenoid, Relay and Actuator Drivers
- DC to DC Converters
- Motor Control

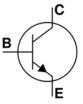
PowerDI3333-8 (SWP) (Type UX)



Top View



**Bottom View** 



Device Symbol

### **Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN03060CFG-7	Standard	2J4	7	12	2,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information

PowerDI3333-8 (SWP) (Type UX)



2J4 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 21 = 2021)

WW = Week Code (01 to 53)



#### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	100	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	Vebo	7	V
Continuous Collector Current	Ic	6	Α
Peak Pulse Current	Ісм	20	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Bower Dissipation	(Note 5)	D-	1.2	W
Power Dissipation	(Note 6)	PD	2.7	W
Thermal Decistores, Junation to Ambient	(Note 5)	D	107	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	- R <sub>θJA</sub>	48	°C/W
Thermal Resistance, Junction to Leads (Note 7)	ReJL	8.5	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### ESD Ratings (Note 8)

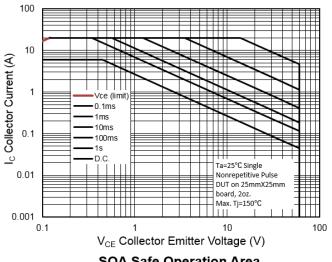
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

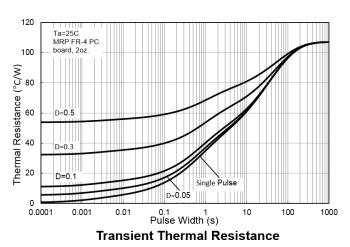
Notes:

- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the collector tab).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

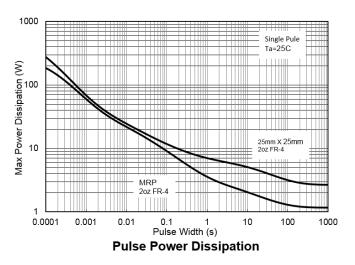


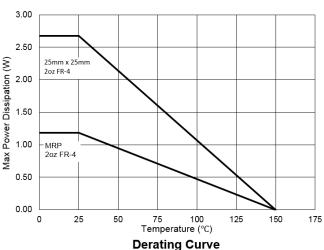
### **Thermal Characteristics and Derating Information**













### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	100	201	_	V	Ic = 100µA
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	60	78	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.9	_	V	I <sub>E</sub> = 100μA
Collector Cut-off Current	Ісво	_	3	50	nA	V <sub>CB</sub> = 100V
Conector Cut-on Current		_	0.2	10	μΑ	V <sub>CB</sub> = 100V, T <sub>A</sub> = +125°C
Collector Cut-off Current	ICER	_	8	50	nA	V <sub>CB</sub> = 80V
Concetor Gut on Gurrent	$R_B \le 1k\Omega$	_	0.3	10	μΑ	V <sub>CB</sub> = 80V, T <sub>A</sub> = +125°C
Emitter Cut-off Current	I <sub>EBO</sub>	_	1	20	nA	V <sub>EB</sub> = 6V
		200	354	_	_	Ic = 10mA, VcE = 2V
		200	357	_	_	Ic = 100mA, VcE = 2V
DC Current Gain (Note 9)	h <sub>FE</sub>	200	343	800	_	$I_C = 1A$ , $V_{CE} = 2V$
		200	325	_	_	Ic = 2A, VcE = 2V
		75	133		_	Ic = 5A, VcE = 2V
	VCE(sat)	_	13	30	mV	Ic = 100mA, I <sub>B</sub> = 5mA
		_	37	60	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Collector-Emitter Saturation Voltage (Note 9)		_	43	70	mV	Ic = 1A, I <sub>B</sub> = 50mA
		_	88	135	mV	Ic = 2A, I <sub>B</sub> = 50mA
		_	194	260	mV	I <sub>C</sub> = 6A, I <sub>B</sub> = 300mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE</sub> (sat)	_	1000	1100	mV	Ic = 6A, I <sub>B</sub> = 300mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	_	930	1050	mV	Ic = 6A, VcE = 1V
Input Capacitance	Cibo	_	509	_	pF	V <sub>EB</sub> = 0.5V. f = 1MHz
Output Capacitance	C <sub>obo</sub>	_	290	_	pF	V <sub>CB</sub> = 10V. f = 1MHz
Current Gain-Bandwidth Product	ft	_	140	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
	t <sub>delay</sub>	_	16.5	_	ns	
Switching Time	trise	_	5.8	_	ns	$I_C = 1A, V_{CC} = 10V,$
Switching riffle	t <sub>storage</sub>	_	1273	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$
	t <sub>fall</sub>	_	27.5	_	ns	

Note:

9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



640

560

480

400

ng 320

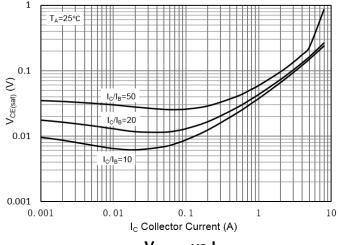
160

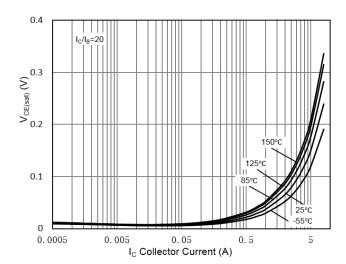
80

0

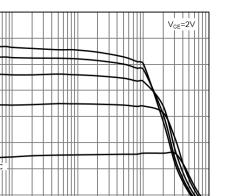
0.001

### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

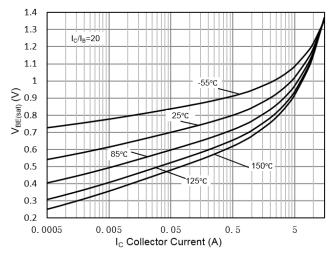








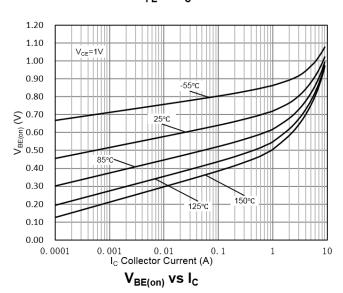
 $V_{\text{CE(sat)}} vs I_{\text{C}}$ 



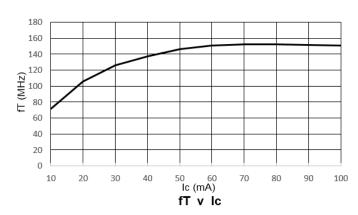
 $I_C$  Collector Current (A)  $h_{FE}$  VS  $I_C$ 

0.1

0.01



 $V_{\text{BE(sat)}} \text{ vs } I_{\text{C}}$ 

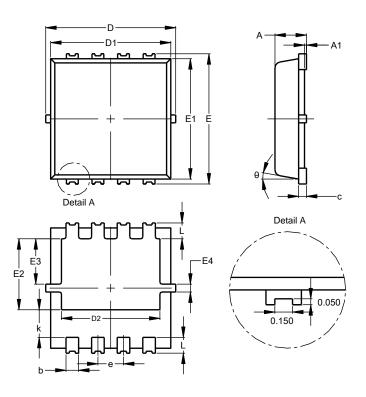




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)

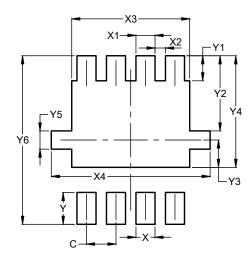


PowerDI3333-8 (SWP)					
(Type UX) ´					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	-		
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	-	-	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Χ	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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